

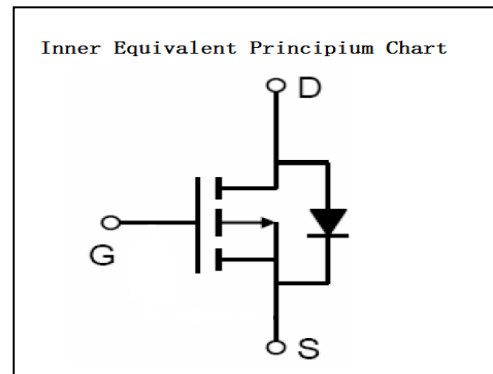
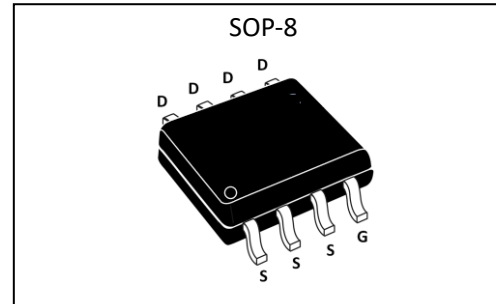
**Features:**

- $R_{DS(ON)} < 14m\Omega$  @  $V_{GS}=10V$  (Typ11m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

|                  |     |            |
|------------------|-----|------------|
| $V_{DSS}$        | -30 | V          |
| $I_D$            | -12 | A          |
| $P_D$            | 3.0 | W          |
| $R_{DS(ON)type}$ | 11  | m $\Omega$ |

**Applications:**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



**Absolute** ( $T_c = 25^\circ C$  unless otherwise specified) :

| Symbol         | Parameter  | Rating          | Units      |
|----------------|--|-----------------|------------|
| $V_{DSS}$      | Drain-to-Source Voltage                          | -30             | V          |
| $I_D$          | Continuous Drain Current                         | -12             | A          |
|                | Continuous Drain Current $T_C = 70^\circ C$      | -10             | A          |
| $I_{DM}^{a1}$  | Pulsed Drain Current                             | -48             | A          |
| $V_{GS}$       | Gate-to-Source Voltage                           | $\pm 20$        | V          |
| $E_{as}^{a5}$  | $L=0.5mH$  | 140             | mJ         |
| $dv/dt^{a3}$   | Peak Diode Recovery $dv/dt$                      | 5.0             | V/ns       |
| $P_D$          | Power Dissipation                                | 3.0             | W          |
| $T_J, T_{stg}$ | Operating Junction and Storage Temperature Range | 150, -55 to 150 | $^\circ C$ |
| $T_L$          | Maximum Temperature for Soldering                | 300             | $^\circ C$ |

**Electrical Characteristics** (Tc= 25°C unless otherwise specified) :

| OFF Characteristics |                                   |   |        |      |      |       |
|---------------------|-----------------------------------|---|--------|------|------|-------|
| Symbol              | Parameter                         | Test Conditions   | Rating |      |      | Units |
|                     |                                   |   | Min.   | Typ. | Max. |       |
| V <sub>DSS</sub>    | Drain to Source Breakdown Voltage | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                        | -30    | --   | --   | V     |
| I <sub>DSS</sub>    | Drain to Source Leakage Current   | V <sub>DS</sub> =-30V, V <sub>GS</sub> = 0V, T <sub>a</sub> =25°C | --     | --   | 1.0  | μA    |
| I <sub>GSS(F)</sub> | Gate to Source Forward Leakage    | V <sub>GS</sub> = +20V  | --     | --   | 0.1  | μA    |
| I <sub>GSS(R)</sub> | Gate to Source Reverse Leakage    | V <sub>GS</sub> =-20V   | --     | --   | -0.1 | μA    |

| ON Characteristics <sup>a3</sup> |                               |  |        |      |      |       |
|----------------------------------|-------------------------------|--|--------|------|------|-------|
| Symbol                           | Parameter                     | Test Conditions  | Rating |      |      | Units |
|                                  |                               |  | Min.   | Typ. | Max. |       |
| R <sub>DS(ON)</sub>              | Drain-to-Source On-Resistance | V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A              | --     | 11   | 14   | mΩ    |
| V <sub>GS(TH)</sub>              | Gate Threshold Voltage        | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA | -1     | --   | -3.0 | V     |

Pulse width tp ≤ 380μs, δ ≤ 2%

| Dynamic Characteristics <sup>a4</sup> |                              |  |        |      |      |       |
|---------------------------------------|------------------------------|--|--------|------|------|-------|
| Symbol                                | Parameter                    | Test Conditions  | Rating |      |      | Units |
|                                       |                              |  | Min.   | Typ. | Max. |       |
| g <sub>fs</sub>                       | Forward Transconductance     | V <sub>DS</sub> =-5V, I <sub>D</sub> =-10A             | 20     | --   | --   | S     |
| C <sub>iss</sub>                      | Input Capacitance            | V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V<br>f=1.0MHz | --     | 1800 | --   | pF    |
| C <sub>oss</sub>                      | Output Capacitance           |  | --     | 220  | --   |       |
| C <sub>rss</sub>                      | Reverse Transfer Capacitance |  | --     | 180  | --   |       |

| Resistive Switching Characteristics <sup>a4</sup> |                                  |  |        |      |      |       |
|---|----------------------------------|--|--------|------|------|-------|
| Symbol  | Parameter                        | Test Conditions  | Rating |      |      | Units |
|   |                                  |  | Min.   | Typ. | Max. |       |
| t <sub>d(ON)</sub>                                | Turn-on Delay Time               | V <sub>DD</sub> =-15V, I <sub>D</sub> =-10A<br>V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω | --     | 10   | --   | ns    |
| t <sub>r</sub>                                    | Rise Time                        |  | --     | 9    | --   |       |
| t <sub>d(OFF)</sub>                               | Turn-Off Delay Time              |  | --     | 26   | --   |       |
| t <sub>f</sub>                                    | Fall Time                        |  | --     | 11   | --   |       |
| Q <sub>g</sub>                                    | Total Gate Charge                | V <sub>DD</sub> =-15V, I <sub>D</sub> =-10A<br>V <sub>GS</sub> =-10V                     | --     | 25   | --   | nC    |
| Q <sub>gs</sub>                                   | Gate to Source Charge            |  | --     | 4.0  | --   |       |
| Q <sub>gd</sub>                                   | Gate to Drain ( "Miller" )Charge |  | --     | 6    | --   |       |

| Source-Drain Diode Characteristics |  |  |        |      |      |       |
|------------------------------------|--|--|--------|------|------|-------|
| Symbol                             | Parameter  | Test Conditions  | Rating |      |      | Units |
|                                    |  |  | Min.   | Typ. | Max. |       |
| $I_S$                              | Continuous Source Current <sup>a2</sup> (Body Diode) |  | --     | --   | -12  | A     |
| $V_{SD}$                           | Diode Forward Voltage <sup>a3</sup>                  | $I_S = -12A, V_{GS} = 0V$  | --     | --   | -1.5 | V     |
| $t_{rr}$                           | Reverse Recovery Time                                | $I_S = -12A, T_j = 25^\circ C$<br>$di_f/dt = 100A/\mu s,$<br>$V_{GS} = 0V$ | --     | 38   | --   | ns    |
| $Q_{rr}$                           | Reverse Recovery Charge                              |  | --     | 30   | --   | nC    |

| Symbol          | Parameter                      | Typ. | Units        |
|-----------------|--------------------------------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case <sup>a2</sup> | 41.7 | $^\circ C/W$ |

<sup>a1</sup>: Repetitive Rating: Pulse width limited by maximum junction temperature.

<sup>a2</sup>: Surface Mounted on FR4 Board,  $t \leq 10sec$ .

<sup>a3</sup>: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

<sup>a4</sup>: Guaranteed by design, not subject to production

<sup>a5</sup>:  $T_J = 25^\circ C, V_{DD} = 15V, V_G = 10V, L = 0.5Mh$

Typical Electrical and Thermal Characteristics

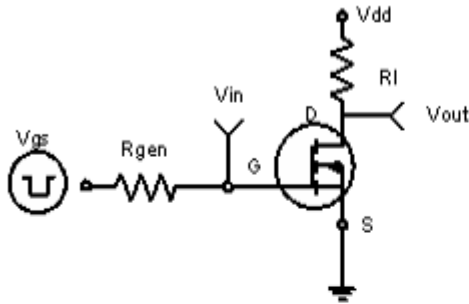


Figure 1: Switching Test Circuit

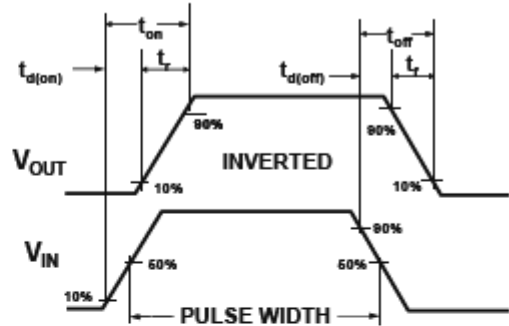


Figure 2: Switching Waveforms

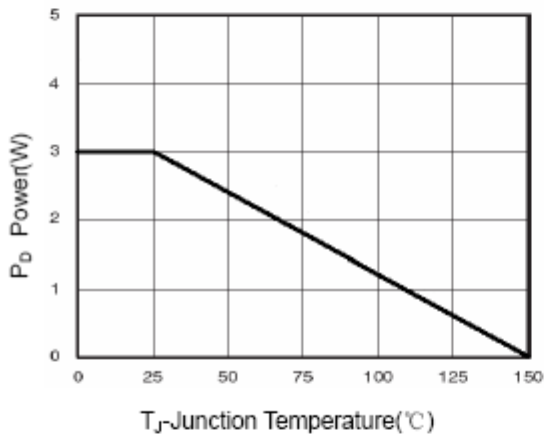


Figure 3 Power Dissipation

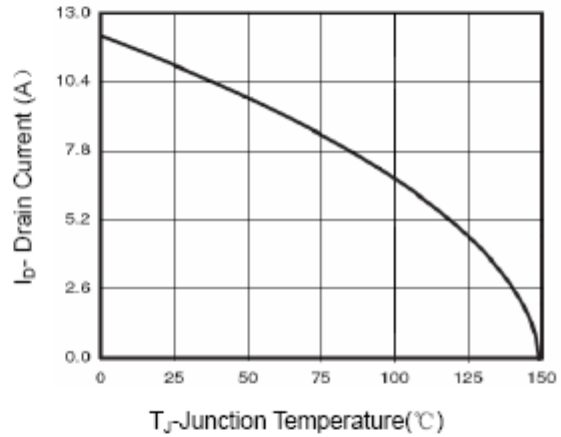


Figure 4 Drain Current

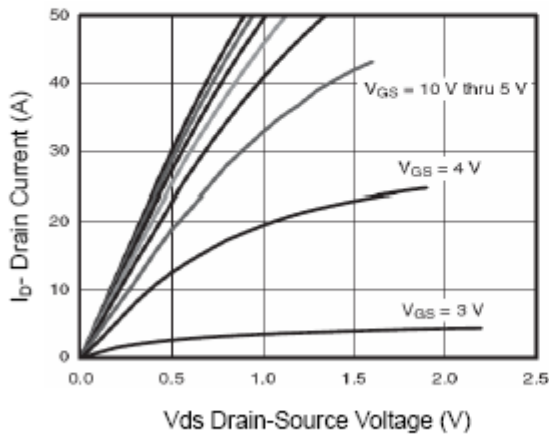


Figure 5 Output Characteristics

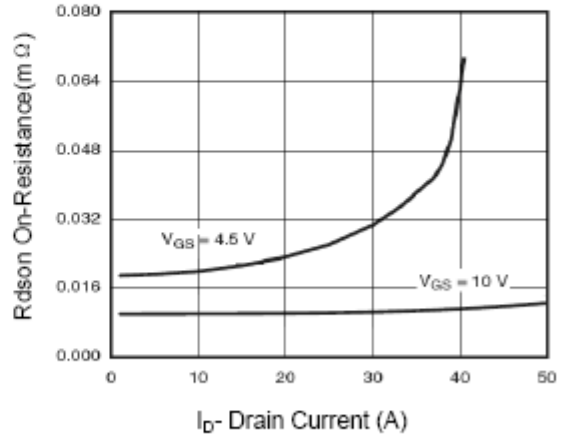
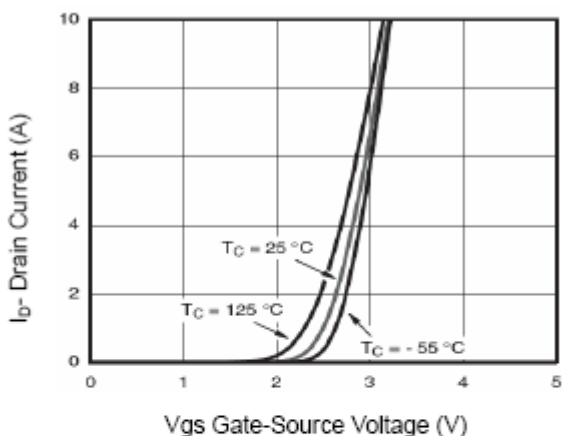
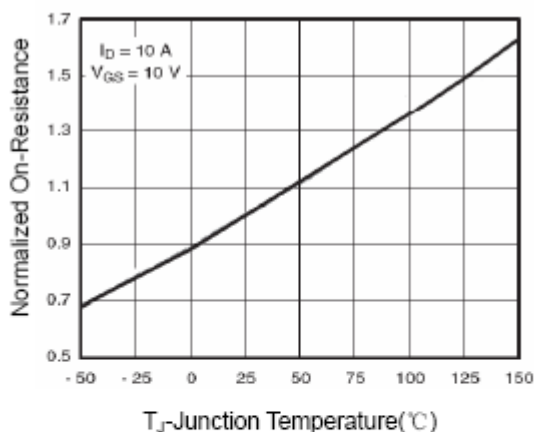


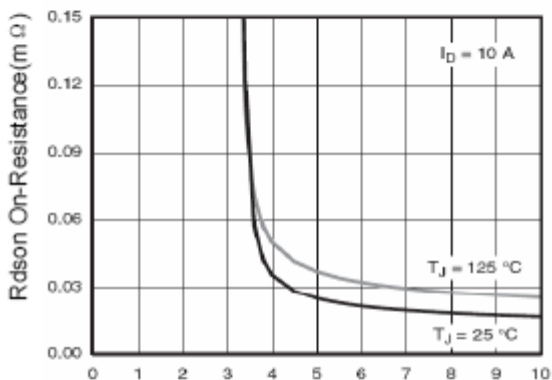
Figure 6 Drain-Source On-Resistance



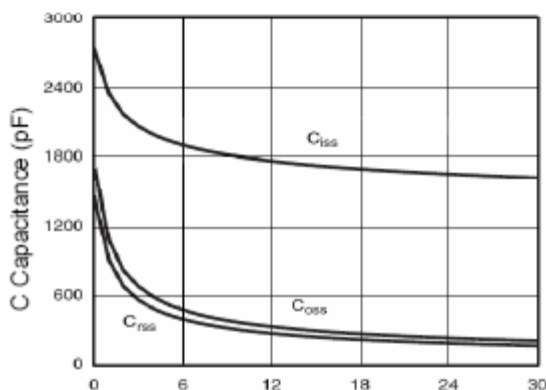
Vgs Gate-Source Voltage (V)  
**Figure 7 Transfer Characteristics**



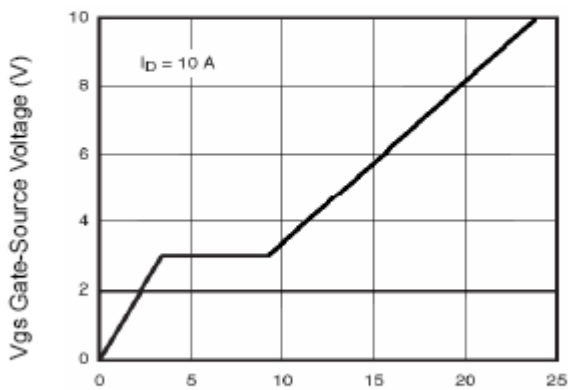
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 8 Drain-Source On-Resistance**



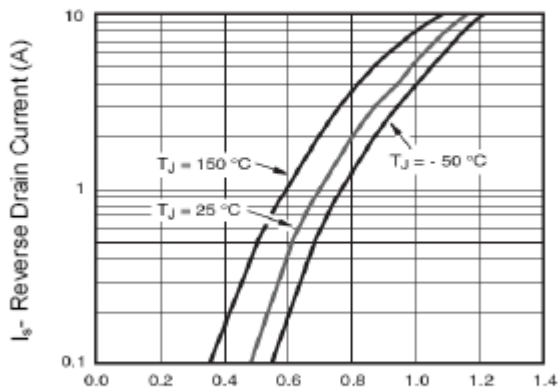
Vgs Gate-Source Voltage (V)  
**Figure 9 Rdson vs Vgs**



Vds Drain-Source Voltage (V)  
**Figure 10 Capacitance vs Vds**



Qg Gate Charge (nC)  
**Figure 11 Gate Charge**



Vsd Source-Drain Voltage (V)  
**Figure 12 Source- Drain Diode Forward**

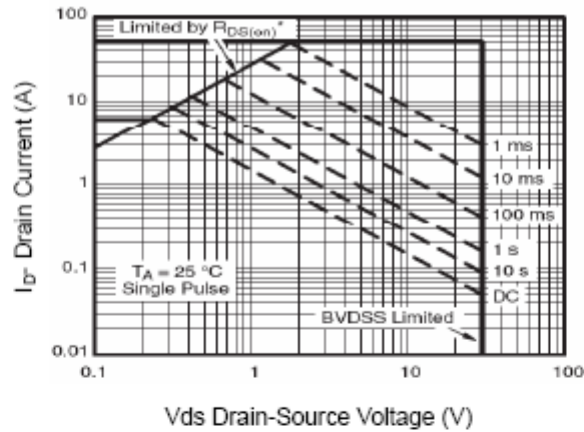


Figure 13 Safe Operation Area

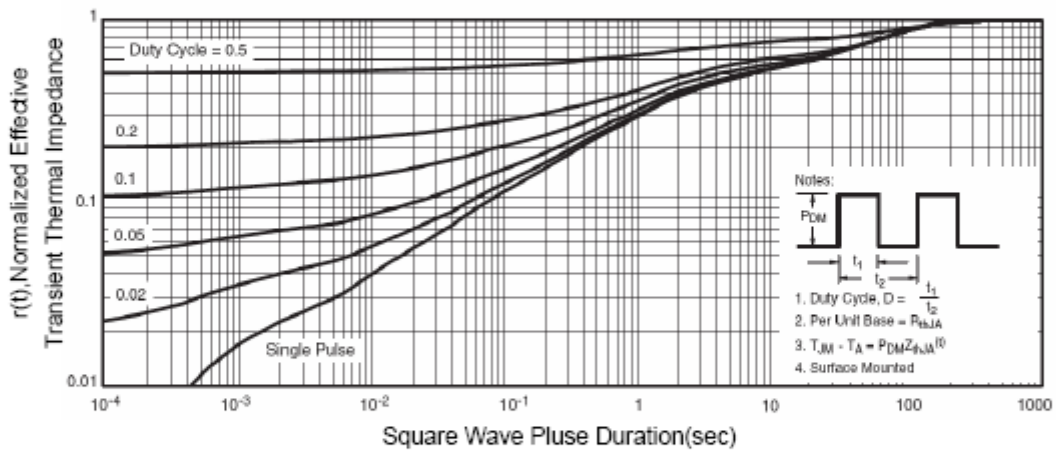


Figure 14 Normalized Maximum Transient Thermal Impedance

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